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June 2016

FCH023N65S3L4

N-Channel SuperFET[®] III MOSFET 650 V, 75 A, 23 m Ω

Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)} = 19.5 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. Q_q = 222 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 1980 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

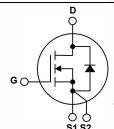
Applications

- Telecom / Server Power Supplies UPS / Solar
- · Industrial Power Supply

Description

SuperFET[®] III MOSFET is Fairchild Semiconductor's brandnew high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SuperFET III MOSFET is suitable for various DC/AC power conversion for system miniaturization and higher efficiency.





S1: Kelvin Source S2: Power Source

Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FCH023N65S3L4	Unit
V _{DSS}	Drain to Source Voltage			650	V
V/	Cata to Course Voltage	- DC		±30	V
V_{GSS}	Gate to Source Voltage	- AC	(f > 1 Hz)	±30	7 V
	Drain Current	- Continuous (T _C = 25°C)		75	^
ID	Drain Current	- Continuous (T _C = 100°C)		65.8	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	300	Α
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	2025	mJ
I _{AR}	Avalanche Current		(Note 1)	15	Α
E _{AR}	Repetitive Avalanche Energy	Repetitive Avalanche Energy (Note 1)		5.95	mJ
du/dt	MOSFET dv/dt			100	V//no
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	20	V/ns
D	Davies Dissination	(T _C = 25°C)	-	595	W
P_{D}	Power Dissipation	- Derate Above 25°C		4.76	W/°C
T _J , T _{STG}	Operating and Storage Temperat	ure Range		-55 to +150	°C
T _L	Maximum Lead Temperature for 1/8" from Case for 5 Seconds	Maximum Lead Temperature for Soldering,			

Thermal Characteristics

Symbol	Parameter FCH023N65S3L4			
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.21	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 40		C/VV	

Package Marking and Ordering Information

	Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
Ī	FCH023N65S3L4	FCH023N65S3L4	TO-247 A04	Tube	N/A	N/A	30 units

Test Conditions

Min.

Тур.

Max.

Unit

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted. Parameter

Off Chara	acteristics					
DV	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^{\circ}\text{C}$	650	-	-	W
BV _{DSS}	Drain to Source Breakdown voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 150^{\circ}\text{C}$	700	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.72	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	-	-	1	^
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 520 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	6.8	-	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

Symbol

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 7.5$ mA	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 37.5 \text{ A}$	-	19.5	23	mΩ
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 37.5 \text{ A}$	-	66	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V,	-	7160	-	pF
C _{oss}	Output Capacitance	f = 1 MHz	-	195	-	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	1980	-	pF
C _{oss(er.)}	Energy Related Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	- \	298	-	
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 37.5 A,	-	222	-	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	54	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	90	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	0.9	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	43	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 400 \text{ V}, I_D = 37.5 \text{ A},$	-	30	-	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_g = 2 Ω	-	130	-	ns
t _f	Turn-Off Fall Time	(Note 4)	-	7	-	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	75	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 37.5 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 37.5 A,	-	600	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	17.9	-	μС

- 1. Repetitive rating: pulse width limited by maximum junction temperature.
- 2. I_{AS} = 15 A, R_G = 25 Ω , starting T_J = 25°C.
- 3. I_{SD} ≤ 75 A, di/dt ≤ 200 A/µs, V_DD \leq BV_DSS, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

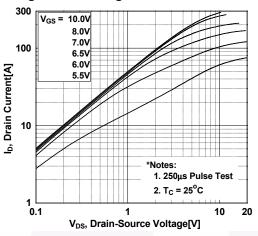


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

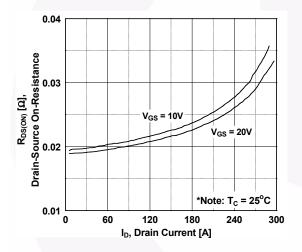


Figure 5. Capacitance Characteristics

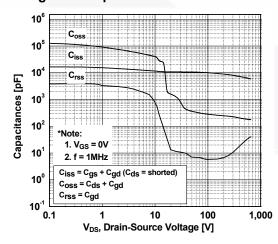


Figure 2. Transfer Characteristics

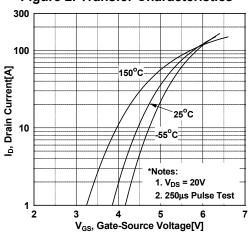


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

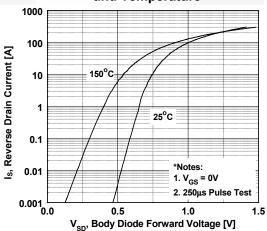
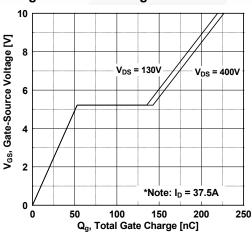


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

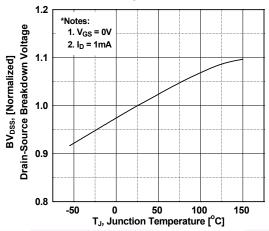


Figure 8. On-Resistance Variation vs. Temperature

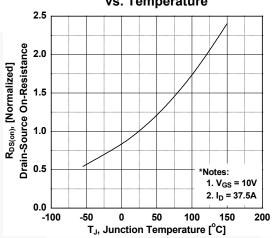


Figure 9. Maximum Safe Operating Area

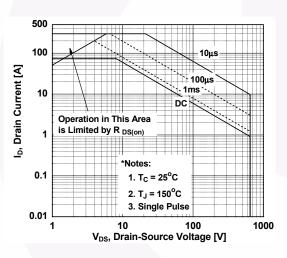


Figure 10. Maximum Drain Current vs. Case Temperature

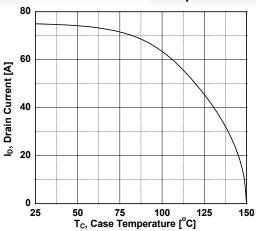
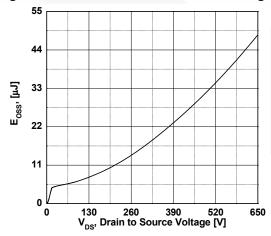
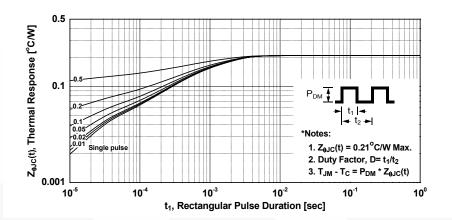


Figure 11. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



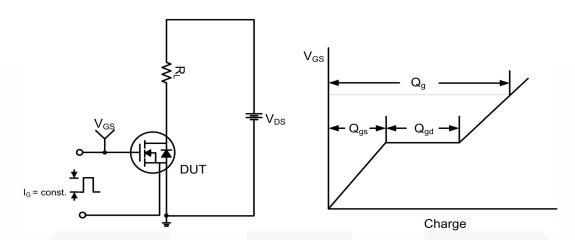


Figure 13. Gate Charge Test Circuit & Waveform

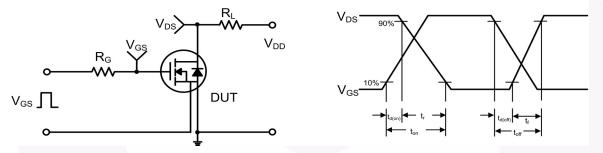


Figure 14. Resistive Switching Test Circuit & Waveforms

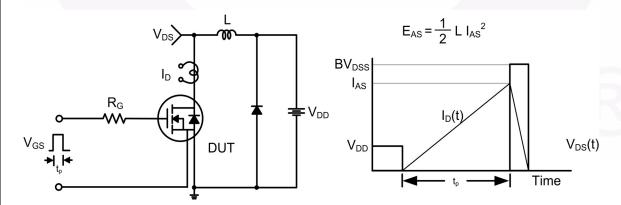


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

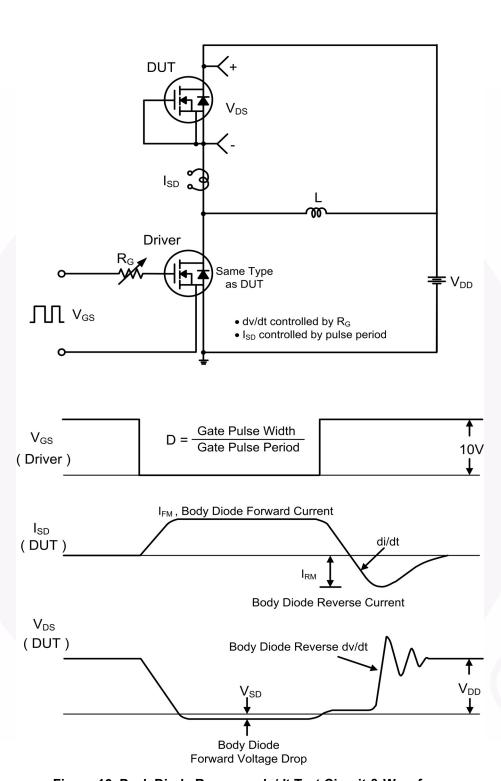
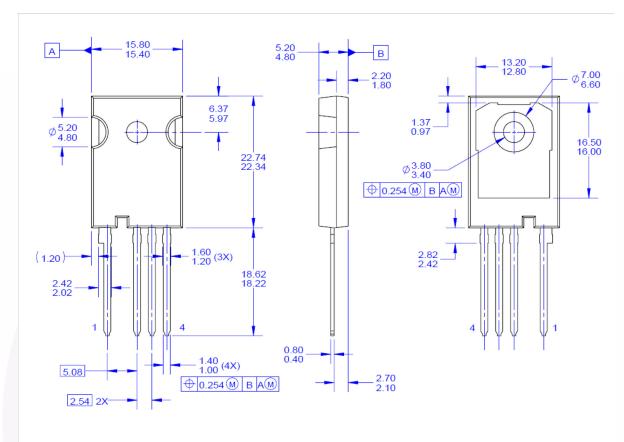


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechnical Dimensions



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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.
- F. DRAWING FILENAME; MKT-TO247A04_REV01.



Figure 17. TO-247 4L - 4LD, T03, PLASTIC, EIAJ SC-65

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